

NIRMA UNIVERSITY
SCHOOL OF TECHNOLOGY, INSTITUTE OF TECHNOLOGY
M.Tech. in Electronics & Communication Engineering (VLSI Design)
M.Tech. Semester - II
Department Elective I

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Course Code	6EC163ME22
Course Title	Characterization of Semiconductor Materials and Devices

Course Learning Outcomes (CLOs):

At the end of the course, students will be able to -

1. Comprehend the concept of material science and impact on device current voltage characteristic.
2. Perform the device characterization.
3. Apply the techniques to reduce the device parasitic.

Syllabus:

Teaching Hours:45

UNIT I: Resistivity	10
Resistivity, four point probe method, resistivity profiling, contact less methods	
UNIT II: Carrier and Doping Density	10
Introduction, Capacitance-Voltage (C-V), Current-Voltage (I-V), Measurement Errors and Precautions, Optical Techniques, Secondary Ion Mass Spectrometry (SIMS), Rutherford Backscattering (RBS), Lateral Profiling, Strengths and Weaknesses, capacitance measurement, current voltage measurements	
UNIT III: Contact Resistance and Schottky Barriers	10
Introduction, Metal-Semiconductor Contacts, Contact Resistance, Measurement Techniques, Comparison of Methods optical techniques, Contact resistance and Schottky barrier height, metal semiconductor contacts, contact resistance measurement techniques	
UNIT IV: Series Resistance Channel Length and Threshold Voltage	05
MESFETs and MODFETs, Pseudo MOSFET Schottky Diode Current-Voltage Equation	
UNIT V: Defects	05
Introduction, Generation-Recombination Statistics, Capacitance Measurements, Current Measurements, Charge Measurements, Deep-Level Transient Spectroscopy (DLTS), Thermally Stimulated Capacitance and Current Positron Annihilation Spectroscopy (PAS) Strengths and Weaknesses, Deep level impurities	
UNIT VI: Characterization	05
Chemical and physical characterization, Electron beam techniques, ion beam techniques, X-ray and gamma ray techniques, Failure Times and Acceleration Factors, Reliability Concerns, Failure Analysis Characterization Techniques	

Self-Study:

The self-study contents will be declared at the commencement of Semester. Around 10% of the questions will be asked from self-study contents.

Suggested Readings:

1. Dieter K. Schroder, Semiconductor Material and Device characterization, John Wiley & Sons
2. S. M. Sze, Modern Semiconductor Device Physics, John Wiley & Sons
3. D. Nagchoudhuri, Microelectronic Devices, Pearson Education